



Supplementary information

Switching characteristics and mechanism using Al₂O₃ interfacial layer in Al/Cu/GdO_x/Al₂O₃/TiN memristor

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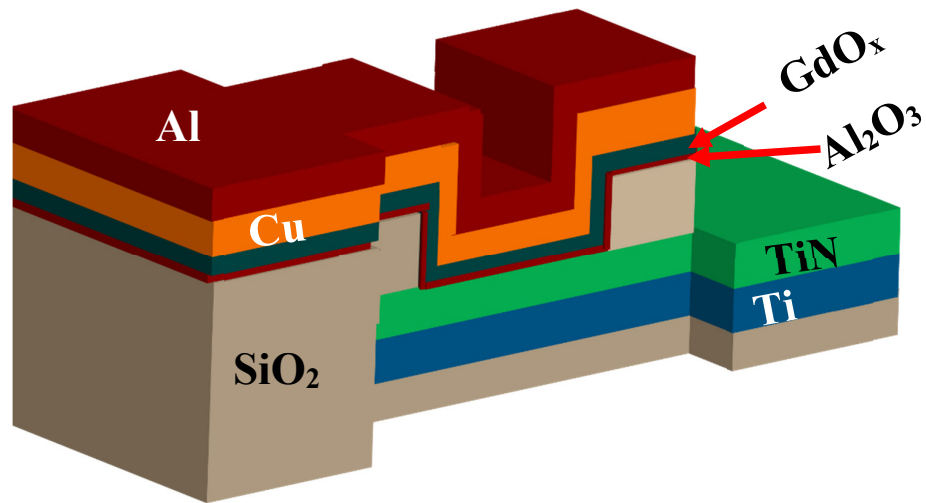


Figure S2: Schematic view of Al/Cu/GdO_x/Al₂O₃/TiN memory structure